



STPS2030CT/CG/CR

LOW DROP POWER SCHOTTKY RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
V_{RRM}	30 V
$T_j \text{ (max)}$	150°C
$V_F \text{ (max)}$	0.40 V

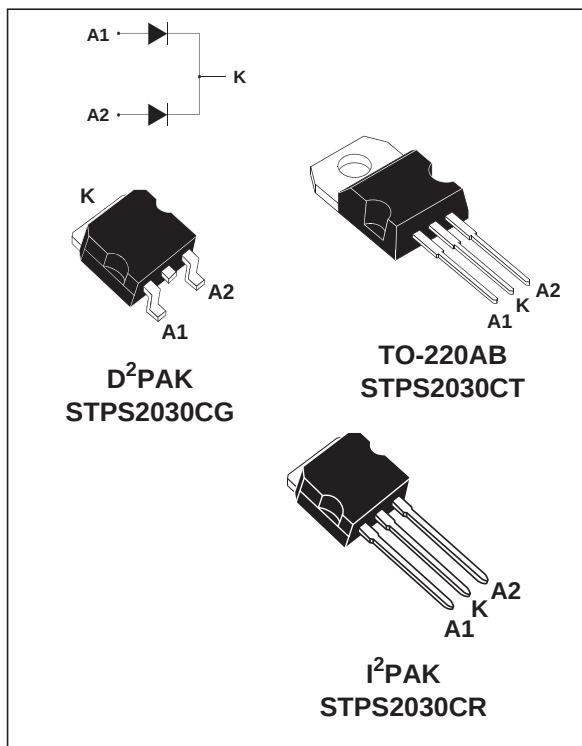
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP FOR HIGHER EFFICIENCY
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual Schottky rectifier suited for switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-220AB, D²PAK and I²PAK, this device is intended for use in low voltage high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			30	V
$I_{F(RMS)}$	RMS forward current			30	A
$I_{F(AV)}$	Average forward current	$T_c = 140^\circ\text{C}$ $\delta = 0.5$	Per diode Per device	10 20	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$	Sinusoidal	180	A
I_{RRM}	Peak repetitive reverse current	$t_p = 2 \mu\text{s}$	square F=1kHz	1	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100 \mu\text{s}$	square	2	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1 \mu\text{s}$	$T_j = 25^\circ\text{C}$	3000	W
T_{stg}	Storage temperature range			- 65 to + 150	°C
T_j	Maximum operating junction temperature *			150	°C
dV/dt	Critical rate of rise of reverse voltage (rated V_R , $T_j = 25^\circ\text{C}$)			10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case TO-220AB - D ² PAK - I ² PAK	Per diode	2.2	°C/W
		Total	1.3	
$R_{th(c)}$		Coupling	0.3	°C/W

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$		0.15	1.0	mA
		$T_j = 125^\circ\text{C}$			80	160	
V_F^*	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 10\text{ A}$		0.44	0.50	V
		$T_j = 125^\circ\text{C}$	$I_F = 10\text{ A}$		0.34	0.40	
		$T_j = 25^\circ\text{C}$	$I_F = 20\text{ A}$		0.50	0.58	
		$T_j = 125^\circ\text{C}$	$I_F = 20\text{ A}$		0.44	0.52	

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.28 \times I_{F(AV)} + 0.012 I_{F(RMS)}^2$$

Fig. 1: Conduction losses versus average current.

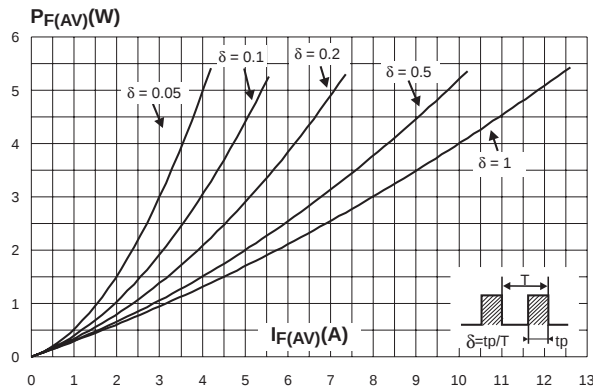


Fig. 3: Normalized avalanche power derating versus pulse duration.

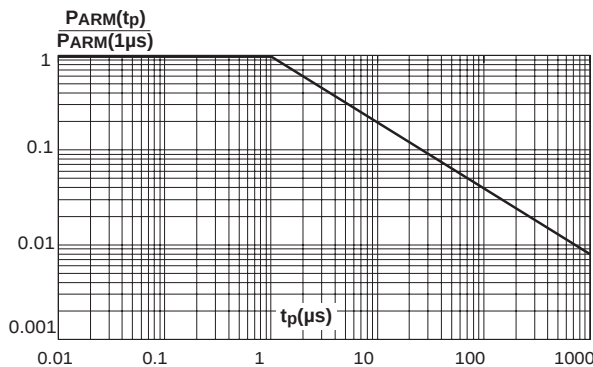


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$).

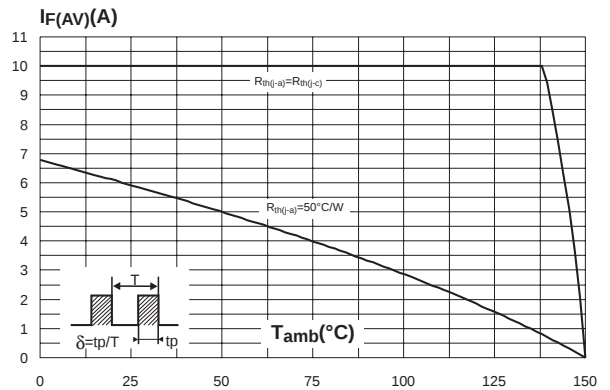


Fig. 4: Normalized avalanche power derating versus junction temperature.

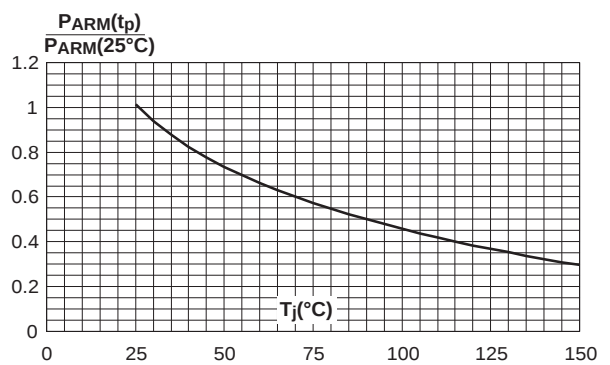


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

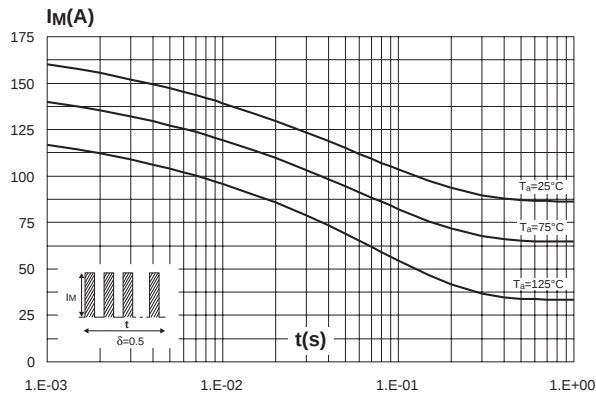


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

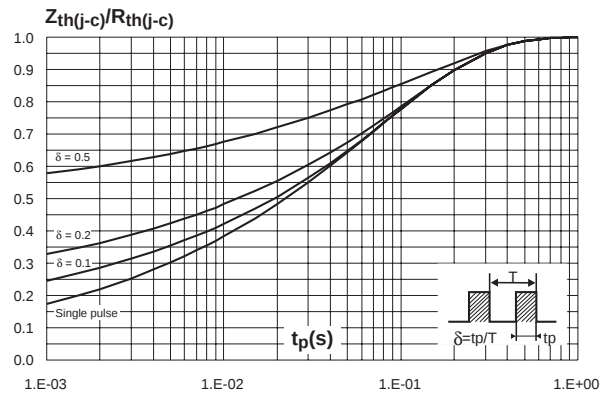


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

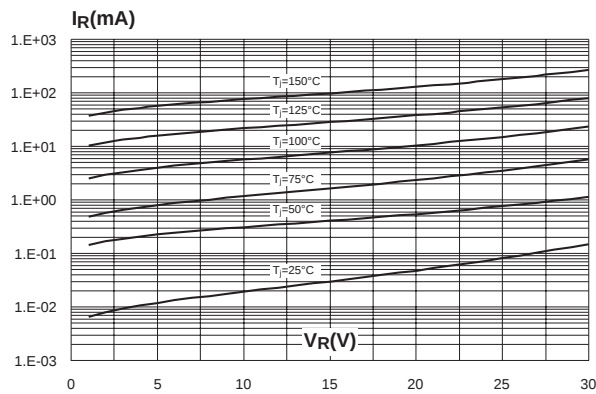


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

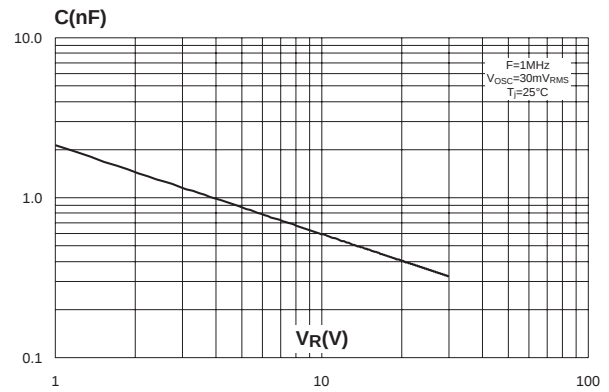


Fig. 9: Forward voltage drop versus forward current.

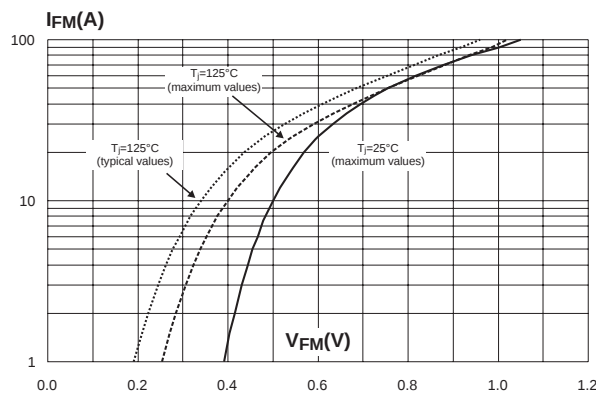
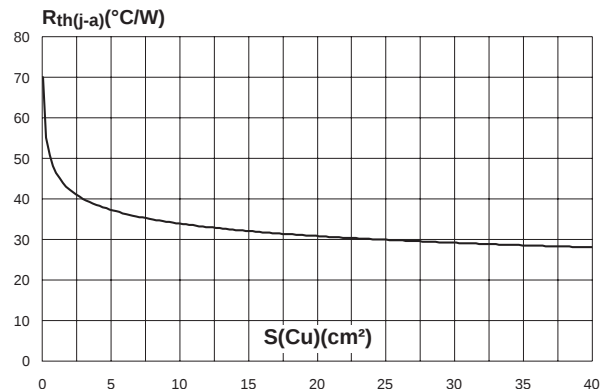
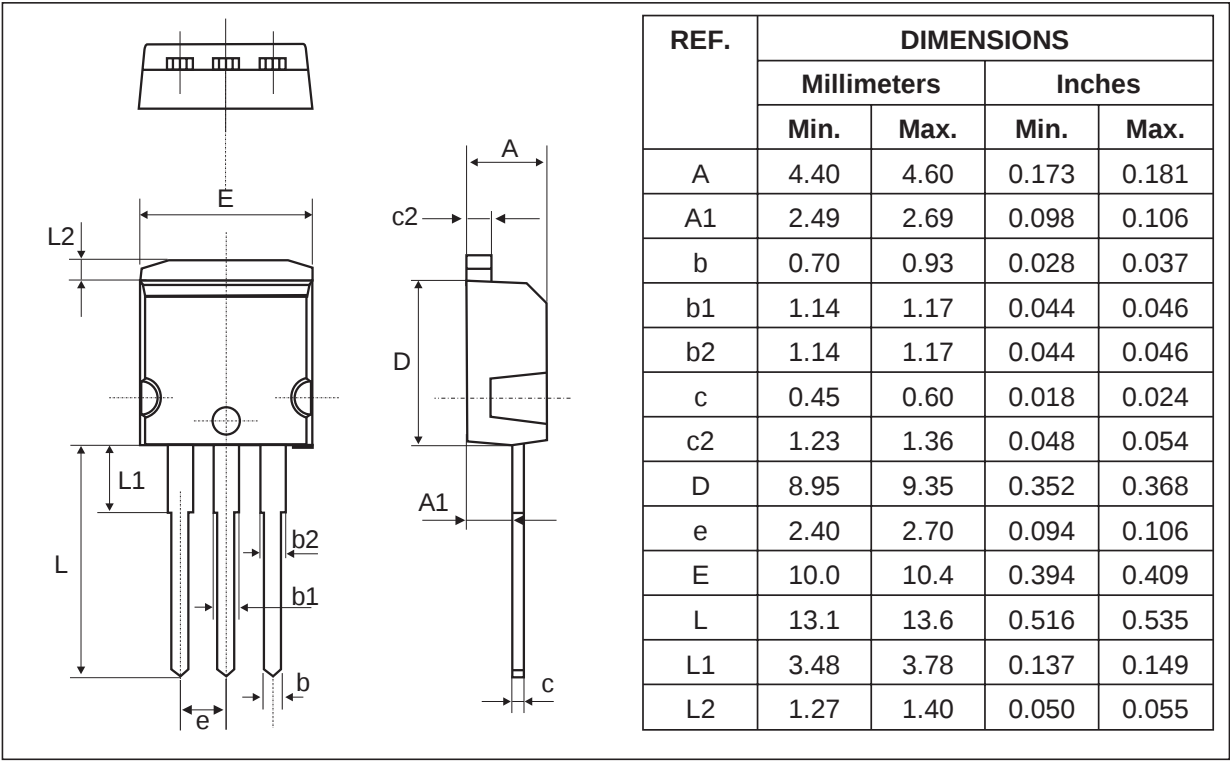


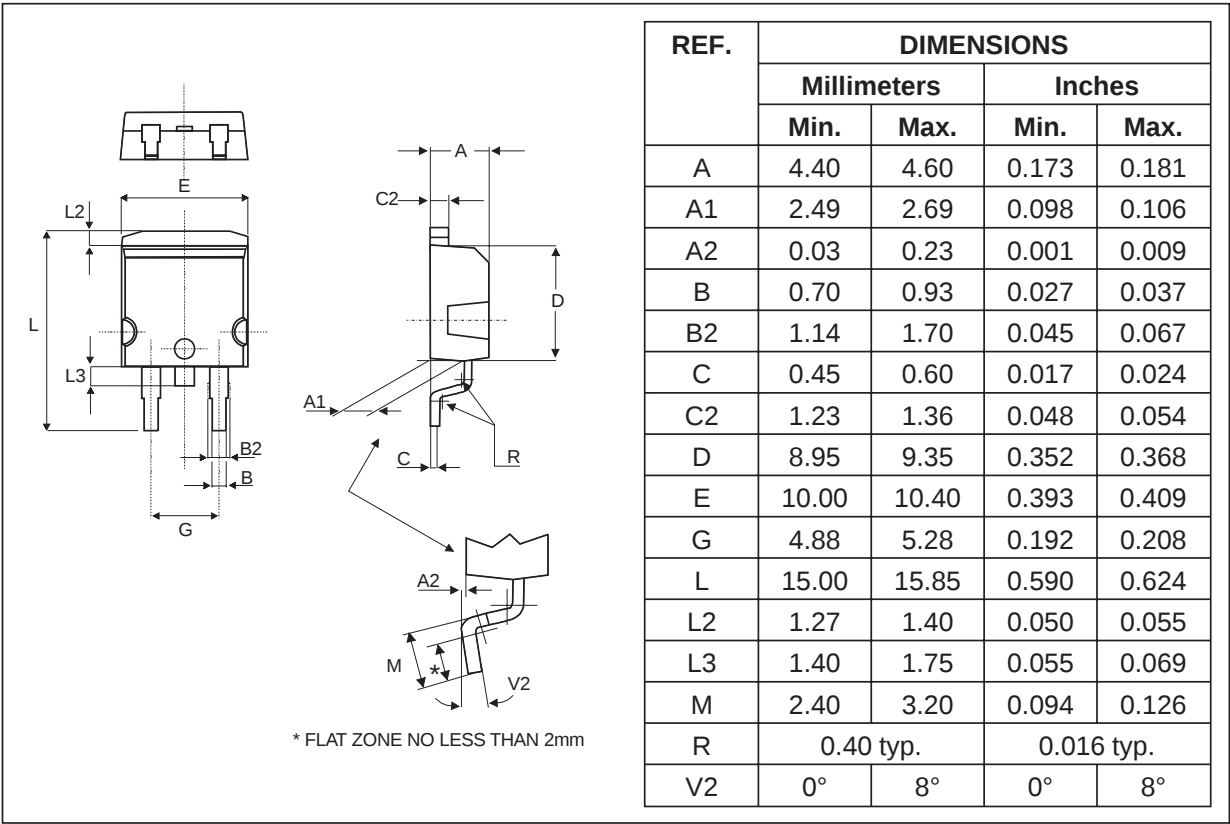
Fig. 10: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4, Cu = 35 μm).



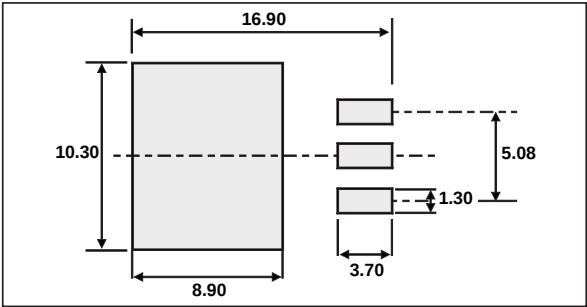
PACKAGE MECHANICAL DATA
I²PAK

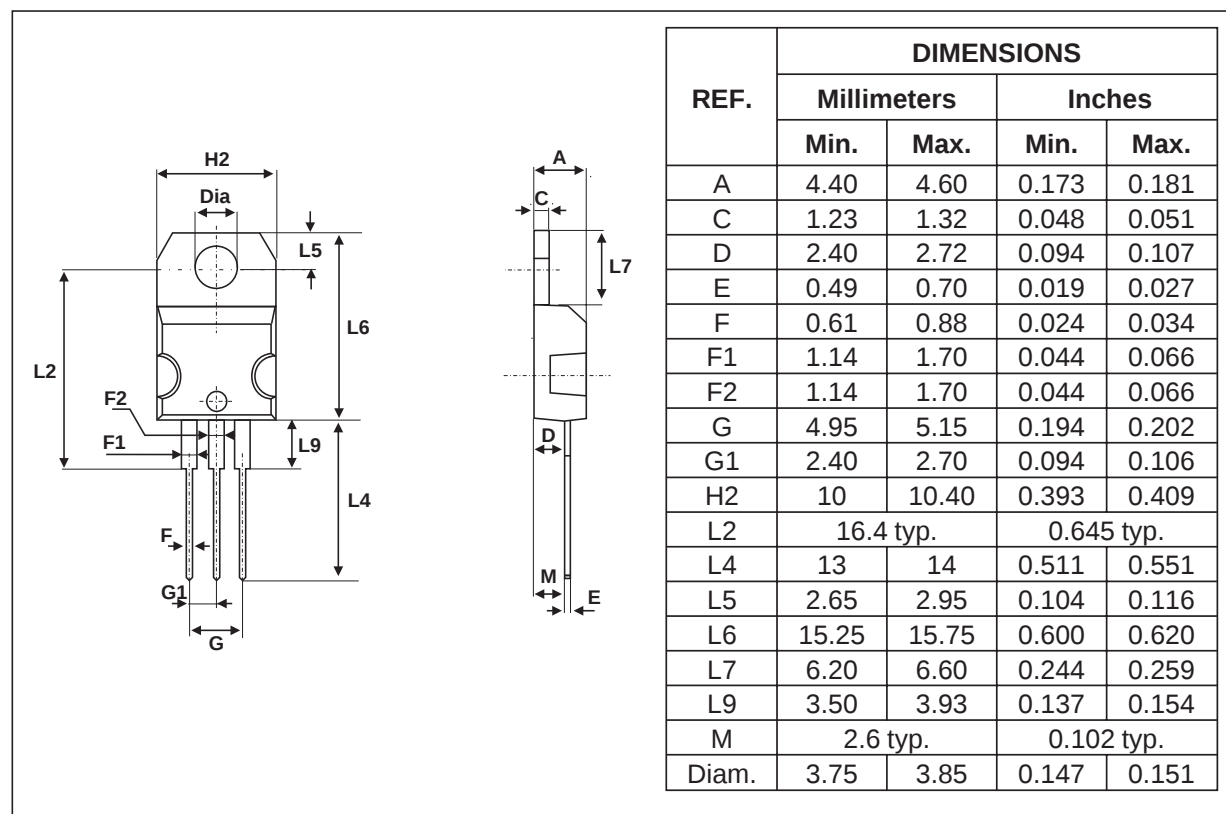


PACKAGE MECHANICAL DATA
D²PAK



FOOTPRINT



PACKAGE MECHANICAL DATA
 TO-220AB


- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.55 M.N
- MAXIMUM TORQUE VALUE : 0.70 M.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS2030CT	STPS2030CT	TO-220AB	2.2 g	50	Tube
STPS2030CG	STPS2030CG	D ² PAK	1.48 g	50	Tube
STPS2030CG-TR	STPS2030CG	D ² PAK	1.48 g	1000	Tape & reel
STPS2030CR	STPS2030CR	I ² PAK	1.49 g	50	Tube

- EPOXY MEETS UL94,V0

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